

Device Modeling Report

COMPONENTS: Light-Emitting Diode (LED) Professional
PART NUMBER: OSWT5111A
MANUFACTURER: OPTO SUPPLY
REMARK: TA=0 degree C

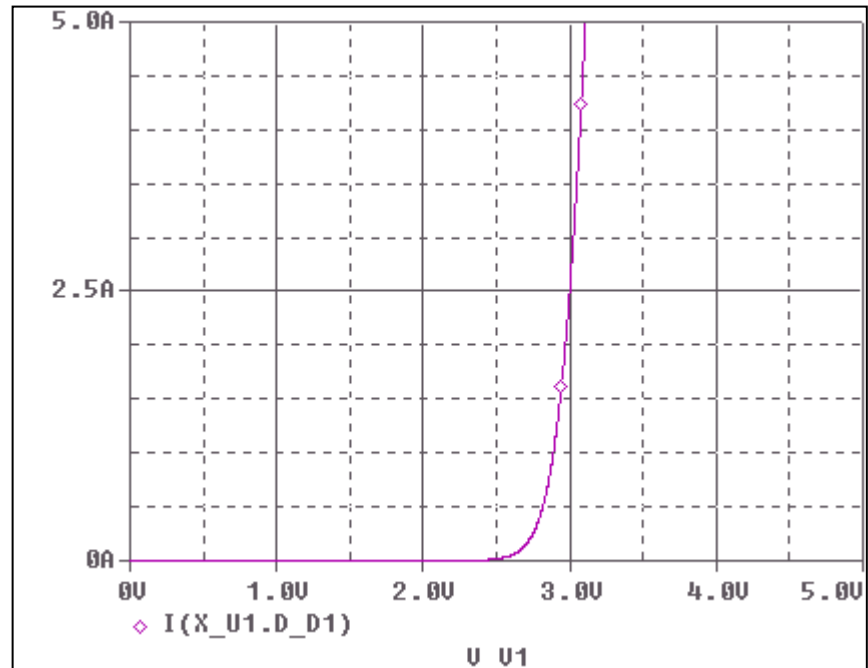


Bee Technologies Inc.

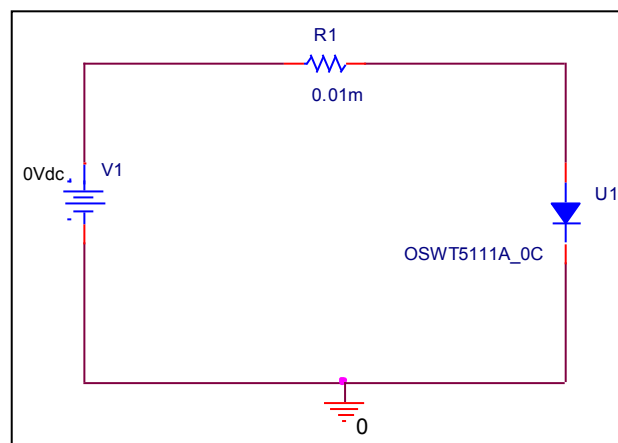
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

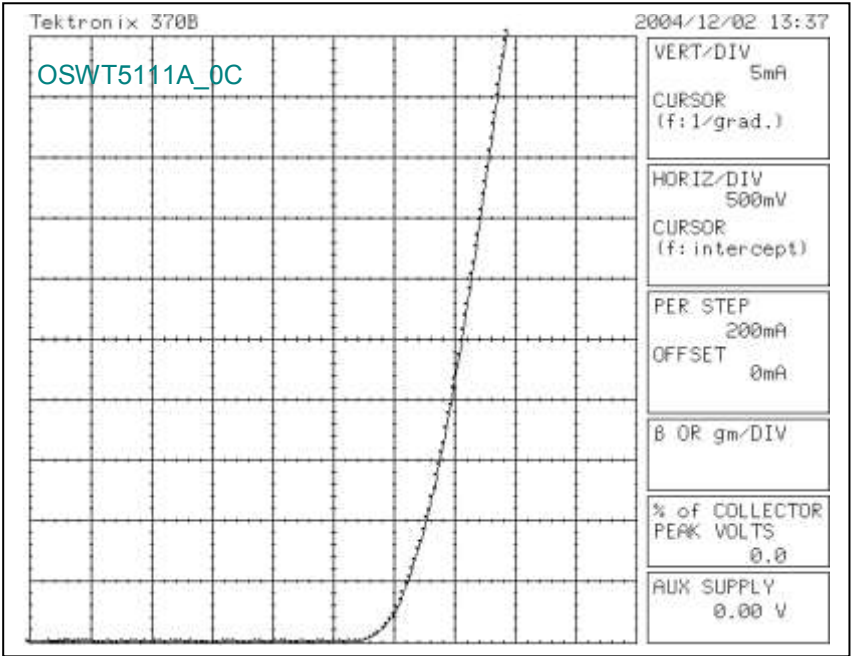


Evaluation Circuit



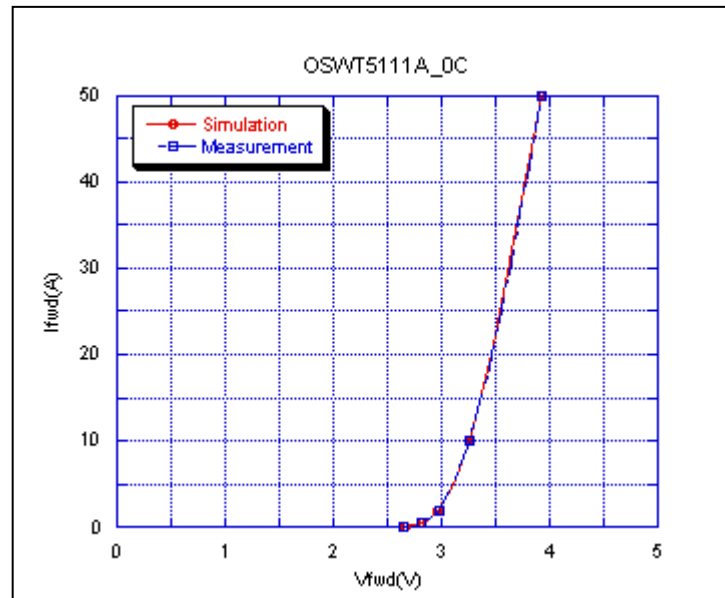
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

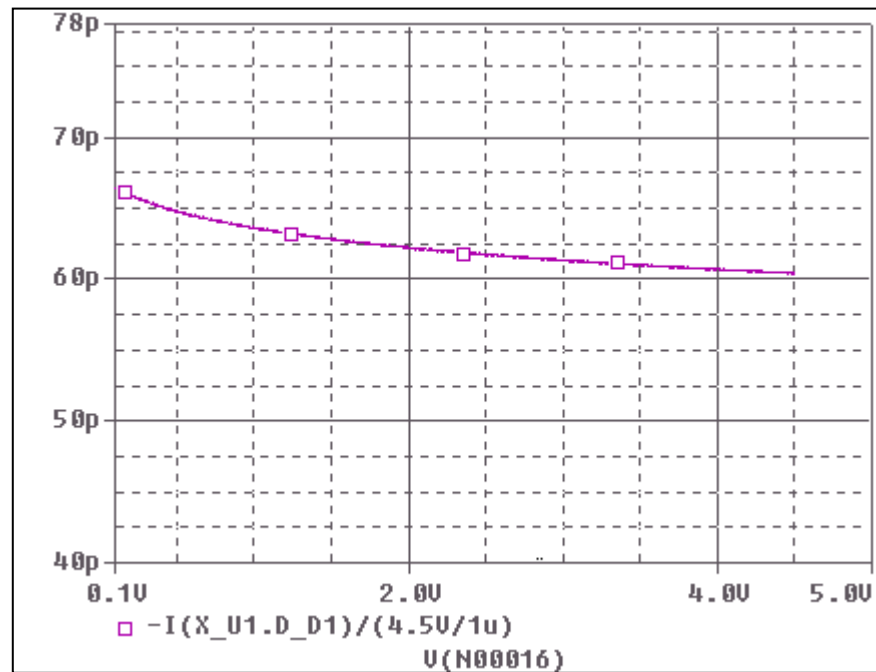


Simulation Result

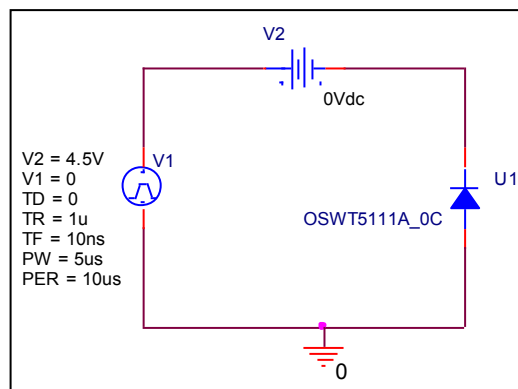
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.1	2.645	2.661	0.6049
0.2	2.725	2.726	0.0366
0.5	2.81	2.815	0.1779
1	2.875	2.887	0.4173
2	2.975	2.969	0.2016
5	3.11	3.107	0.0964
10	3.25	3.255	0.1538
20	3.47	3.467	0.0864
50	3.92	3.923	0.0765

Capacitance Characteristic

Circuit Simulation Result

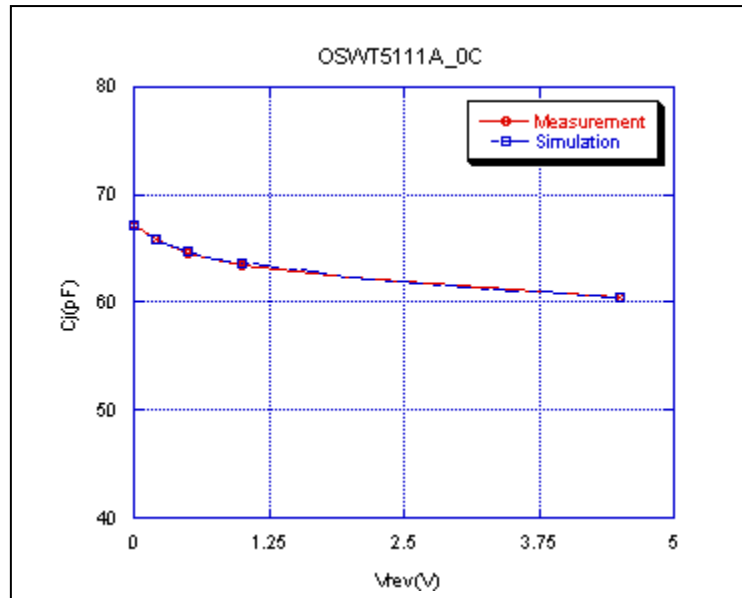


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

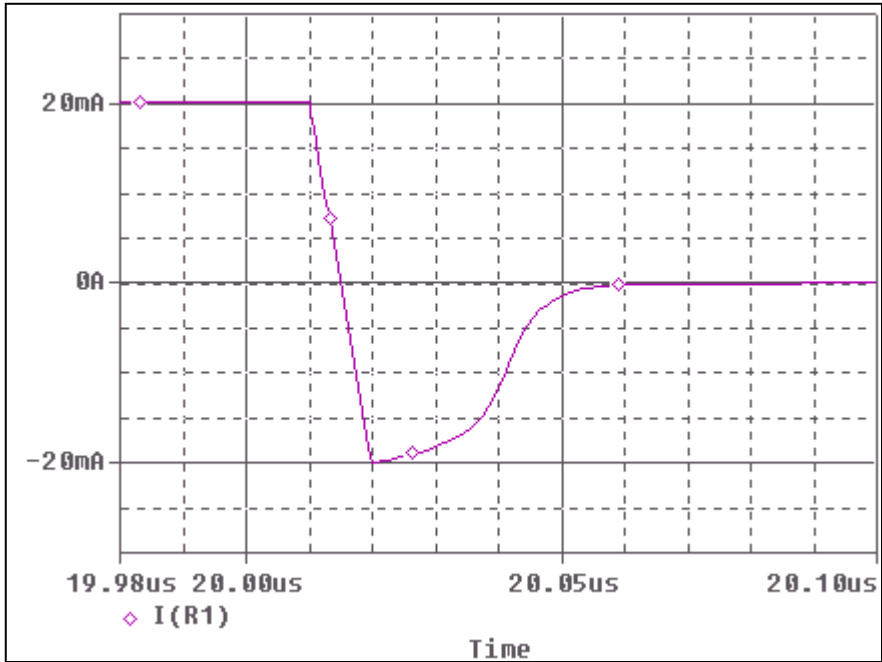


Simulation Result

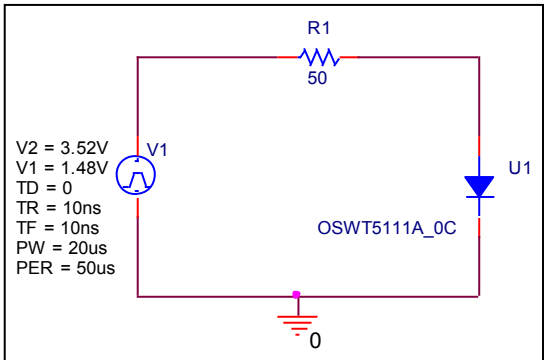
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	67.1	67.1	0
0.1	66.55	66.428	0.1833
0.2	65.88	65.851	0.0440
0.5	64.5	64.807	0.4759
1	63.46	63.544	0.1323
2	62.33	62.297	0.0529
4.5	60.515	60.402	0.1867

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

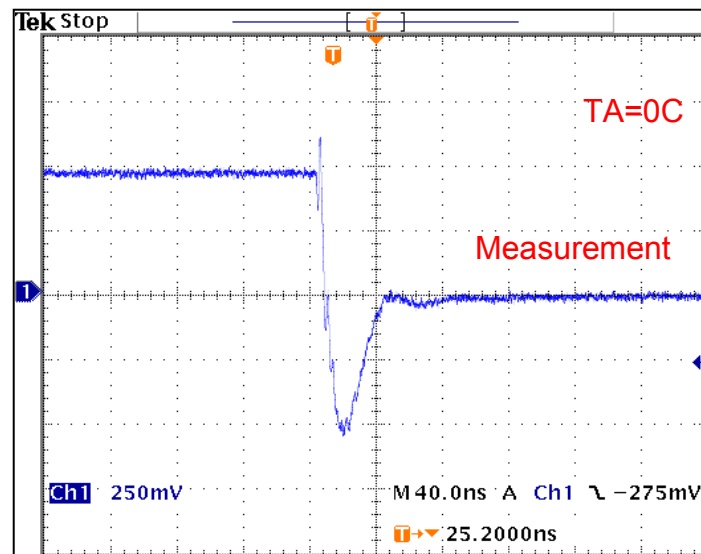


Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
trj	8.8	ns	8.768	ns	0.36363
trb	23.2	ns	24.21	ns	4.35344

Reverse Recovery Characteristic

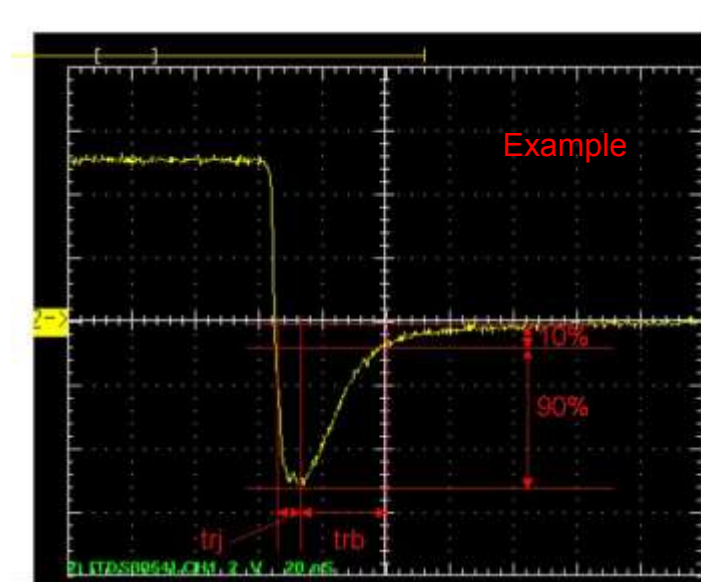
Reference



$T_{rj} = 8.8(\text{ns})$

$T_{rb} = 23.2(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.02(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}